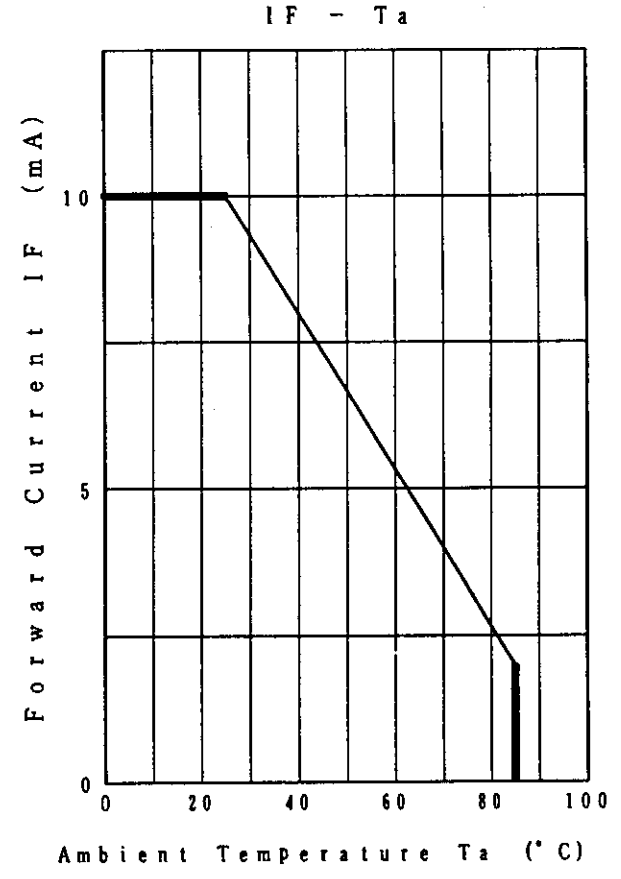
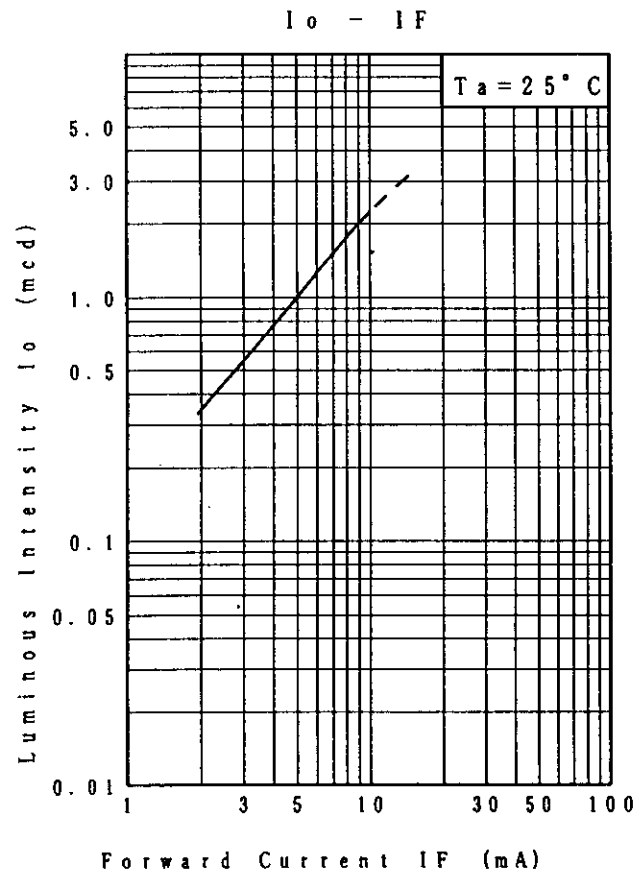
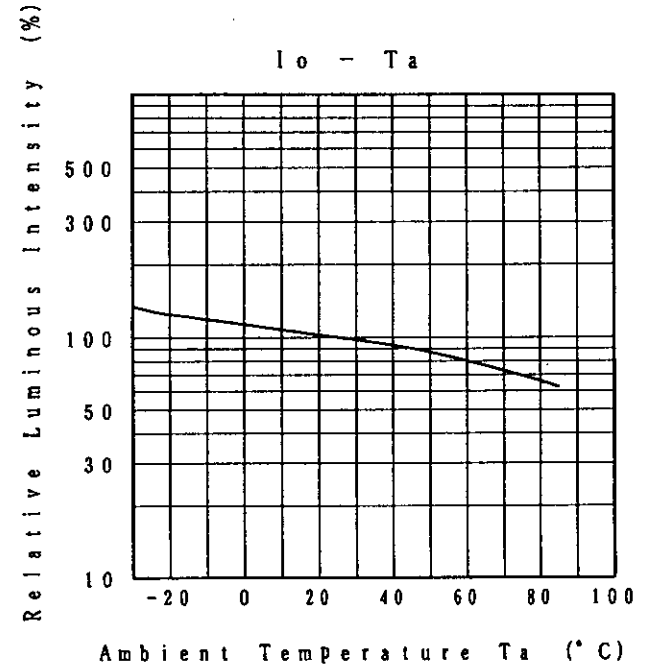
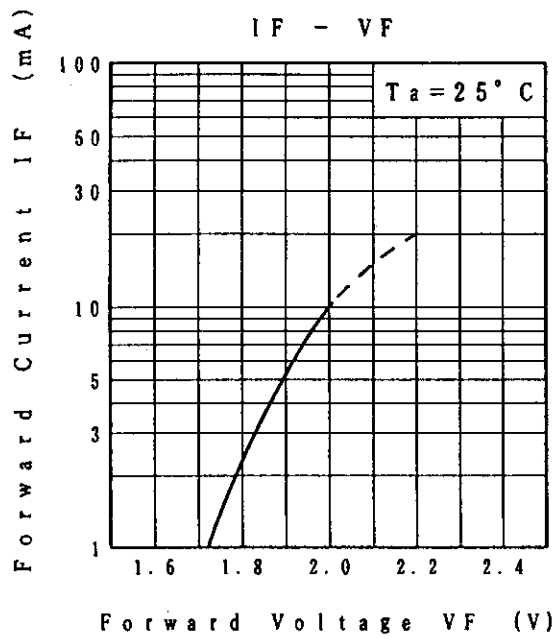


Approved <i>M. Yamashita</i>	Checked <i>M. Kishita</i>	Designed <i>T. Takata</i>	DEVELOPMENT SPECIFICATION					
							P/N: LN1471SYTRP	
T Y P E			Amber Light Emitting Diode					
APPLICATION			Indicators					
MATERIAL			GaAsP					
OUTLINE			Attached					
ABSOLUTE MAXIMUM RATINGS			P 30 mW	※IFP 50 mA	IFDC 10 mA	VR 4 V	Topr -30~+85 °C	Tstg -40~+100 °C
CONDITION			Ta=25±3 °C					
Test Specification								
Item	Symbol	Condition	Typ	Limit		Unit		
				Min	Max			
Forward Voltage	VF	IF= 5 mA	1.9		2.4	V		
Reverse Leakage Current	IR	VR= 4 V			10	μA		
Luminous Intensity	IO	IF= 5 mA · DC	1.0	0.4		mcad		
Peak Emission Wavelength	λp	IF= 5 mA · DC	590			nm		
Spectral Line Half Width	Δλ	IF= 5 mA · DC	30			nm		
<p>※ · The condition of IFP is duty 10 % , Pulse width 1 ms          · Please contact the Panasonic local office if you design at low current (below 0.5 mA DC) or pulse current operation and have any questions.</p> <p>NOTE</p> <p>★1 Soldering conditions. Refer to handling note.</p> <p>★2 Care should be taken that soldering is done within 3-days after opening the dry package and reel.</p> <p>★3 Package:Light yellow diffusion type.</p> <p>★4 Tone of Color is passed over.</p>								
Jun.13.1995								

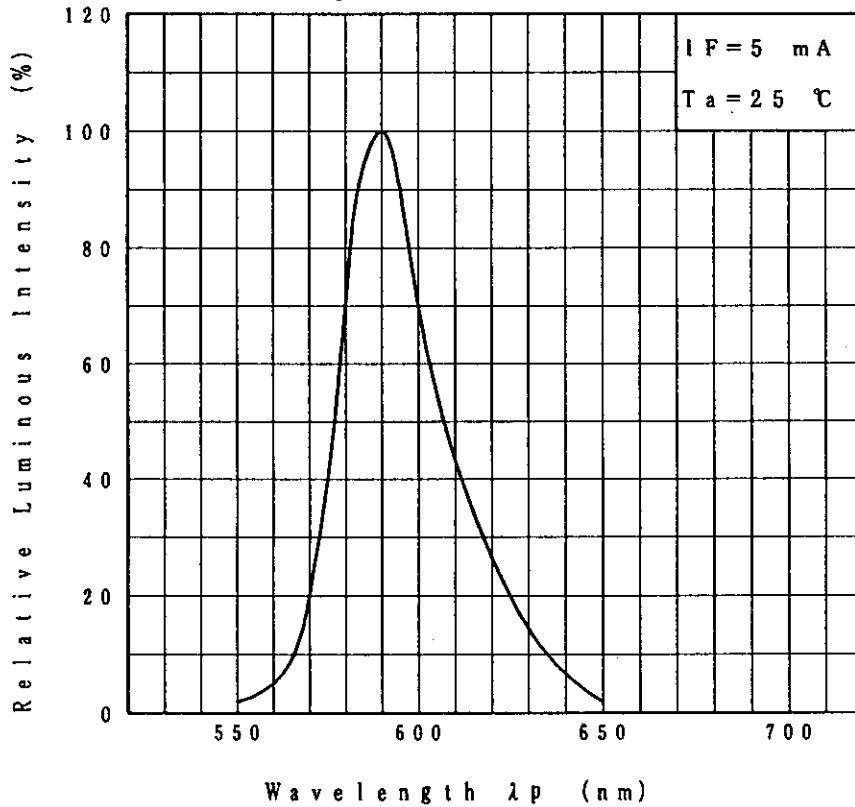


Approved	Checked	Designed
<i>M. Yamashita</i>	<i>K. Kikuchi</i>	<i>T. Takata</i>

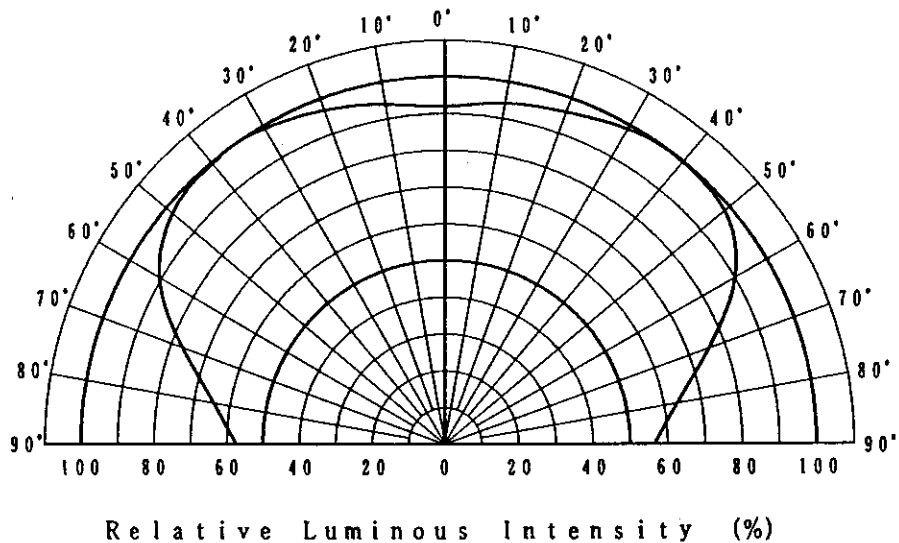
DEVELOPMENT SPECIFICATION

P/N: LN1471SYTRP

Relative Luminous Intensity  
Wavelength Characteristics

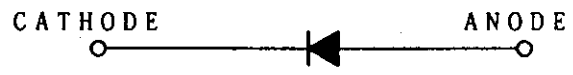
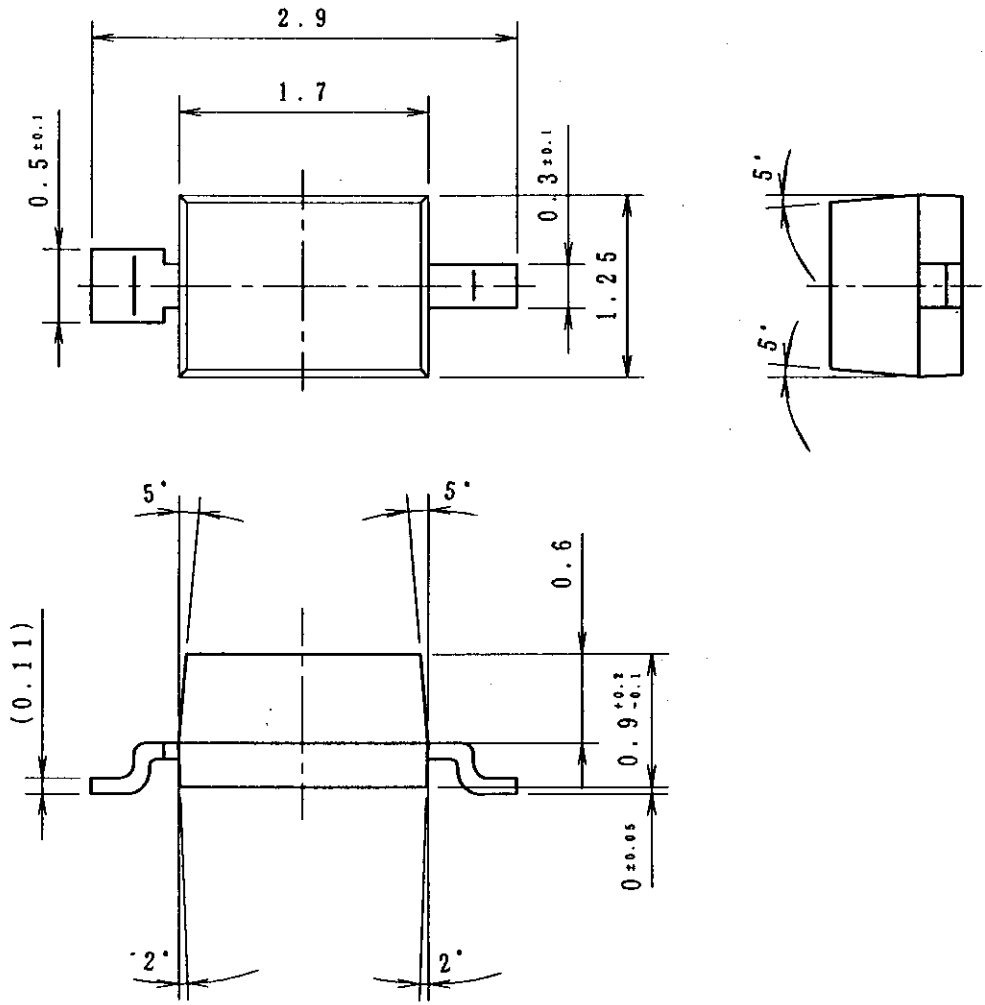


Directive Characteristics



Jun. 13. 1995

Approved <i>M. Yamashita</i>	Checked <i>K. Kubota</i>	Designed <i>T. Takata</i>	<b>DEVELOPMENT SPECIFICATION</b> PN: <u>LN1471SYTRP</u>			



- (NOTE)
1. Unit: mm
  2. Tolerance unless specified is ±0.2.
  3. Measurement of the package doesn't include gate projection.
  4. Corner of the package is R 0.2max.
  5. Projection's tolerance of the package is 0.2max.

单击下面可查看定价，库存，交付和生命周期等信息

[>>Panasonic\(松下\)](#)